



**AOT14N50 / AOTF14N50**  
**500V, 14A N-Channel MOSFET**

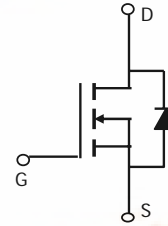
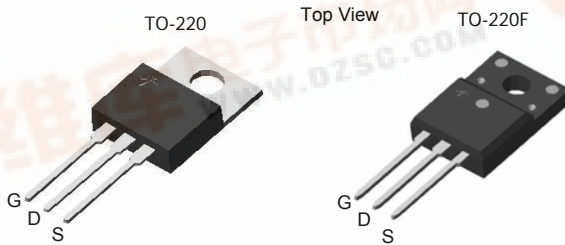
**General Description**

The AOT14N50 & AOTF14N50 have been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications. By providing low  $R_{DS(on)}$ ,  $C_{iss}$  and  $C_{rss}$  along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

**Features**

$V_{DS}$  (V) = 600V@150°C  
 $I_D$  = 14A  
 $R_{DS(on)}$  < 0.38Ω ( $V_{GS} = 10V$ )

**100% UIS Tested!**  
**100%  $R_g$  Tested!**



**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	AOT14N50	AOTF14N50	Units
Drain-Source Voltage	$V_{DS}$	500		V
Gate-Source Voltage	$V_{GS}$	±30		V
Continuous Drain Current	$I_D$	$T_C=25^\circ\text{C}$	14	14*
		$T_C=100^\circ\text{C}$	9.6	9.6*
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	56		A
Avalanche Current <sup>C, G</sup>	$I_{AR}$	6		A
Repetitive avalanche energy <sup>C, G</sup>	$E_{AR}$	540		mJ
Single pulsed avalanche energy <sup>G</sup>	$E_{AS}$	1080		mJ
Peak diode recovery dv/dt	dv/dt	5		V/ns
Power Dissipation <sup>B</sup>	$P_D$	$T_C=25^\circ\text{C}$	223	50
		Derate above 25°C	1.8	0.4
Junction and Storage Temperature Range	$T_J, T_{STG}$	-50 to 150		°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	$T_L$	300		°C

**Thermal Characteristics**

Parameter	Symbol	AOT14N50	AOTF14N50	Units
Maximum Junction-to-Ambient <sup>A, D</sup>	$R_{\theta JA}$	65	65	°C/W
Maximum Case-to-Sink <sup>A</sup>	$R_{\theta CS}$	0.5	--	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	0.56	2.5	°C/W

\* Drain current limited by maximum junction temperature.



AOT14N50 / AOTF14N50

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	500			V
		I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C		600		V
BV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V		0.5		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =500V, V <sub>GS</sub> =0V			1	μA
		V <sub>DS</sub> =400V, T <sub>J</sub> =125°C			10	
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	3.3	4.2	4.5	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =7A		0.29	0.38	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =40V, I <sub>D</sub> =7A		20		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.71	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				14	A
I <sub>SM</sub>	Maximum Body-Diode Pulsed Current				56	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	1531	1914	2297	pF
C <sub>oss</sub>	Output Capacitance		153	191	229	
C <sub>rss</sub>	Reverse Transfer Capacitance		11	16	20	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	1.75	3.5	5.3	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =400V, I <sub>D</sub> =14A		42.8	51	nC
Q <sub>gs</sub>	Gate Source Charge		9.3	11		
Q <sub>gd</sub>	Gate Drain Charge		20.3	24		
t <sub>D(on)</sub>	Turn-On Delay Time	V <sub>GS</sub> =10V, V <sub>DS</sub> =250V, I <sub>D</sub> =14A, R <sub>G</sub> =25Ω		44	53	ns
t <sub>r</sub>	Turn-On Rise Time		84	101		
t <sub>D(off)</sub>	Turn-Off Delay Time		92	110		
t <sub>f</sub>	Turn-Off Fall Time		50	60		
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =14A, dI/dt=100A/μs, V <sub>DS</sub> =100V		289	347	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =14A, dI/dt=100A/μs, V <sub>DS</sub> =100V		4.93	6	μC

A: The value of R<sub>θJA</sub> is measured with the device in a still air environment with T<sub>A</sub>=25°C.

B: The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C, Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25°C.

D: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F: These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150°C. The SOA curve provides a single pulse rating.

G: L=60mH, I<sub>AS</sub>=6A, V<sub>DD</sub>=50V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

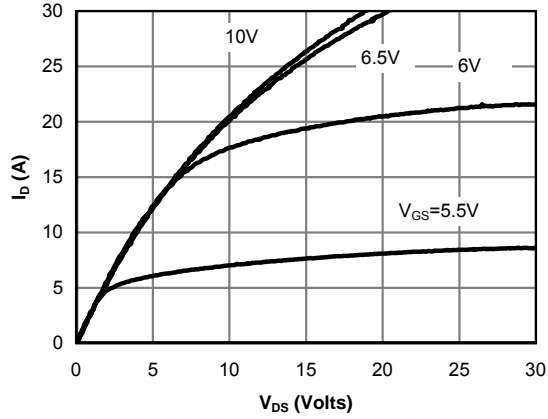


Fig 1: On-Region Characteristics

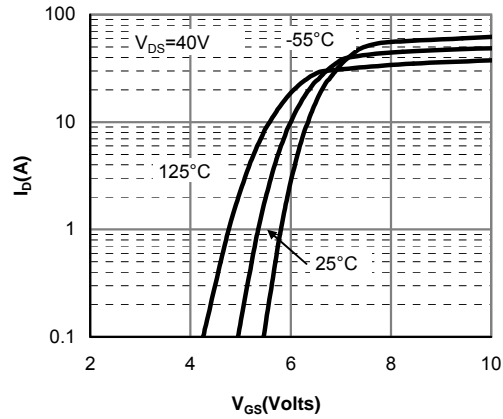


Figure 2: Transfer Characteristics

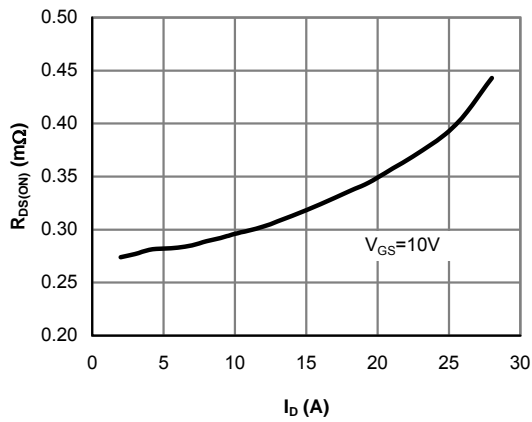


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

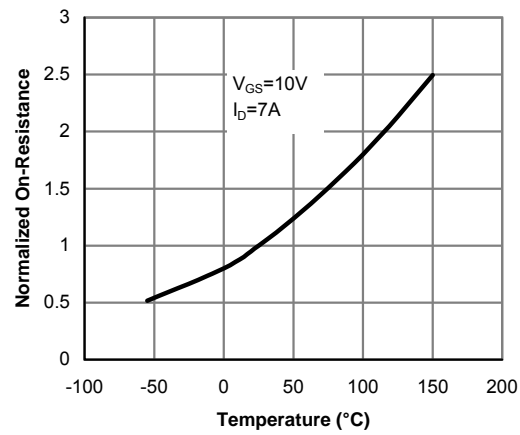


Figure 4: On-Resistance vs. Junction Temperature

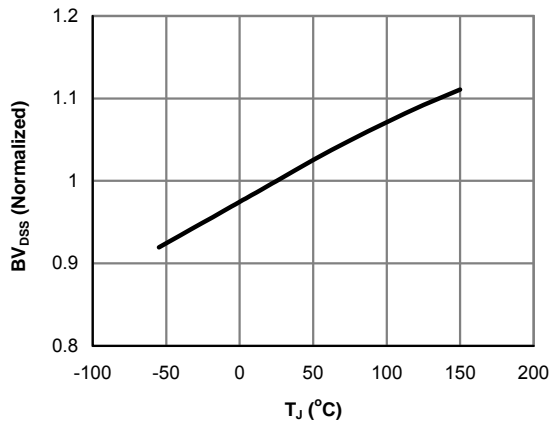


Figure 5: Break Down vs. Junction Temperature

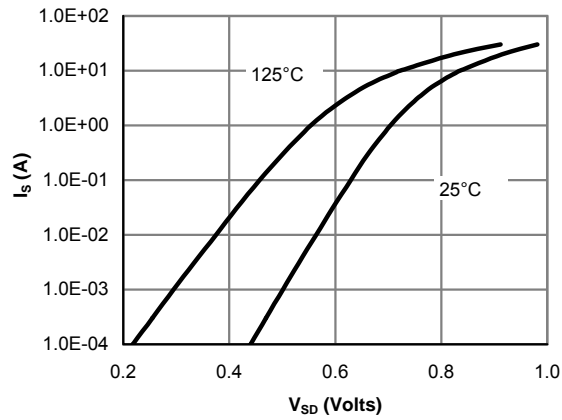


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

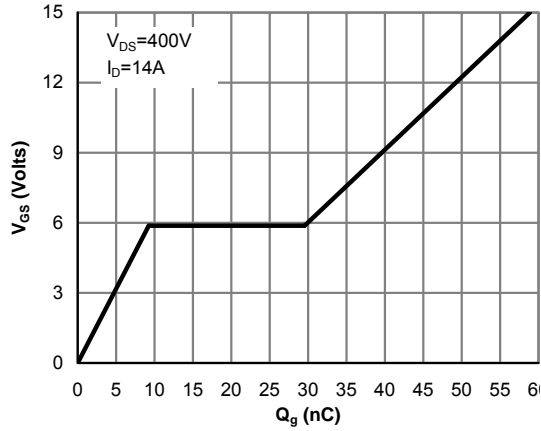


Figure 7: Gate-Charge Characteristics

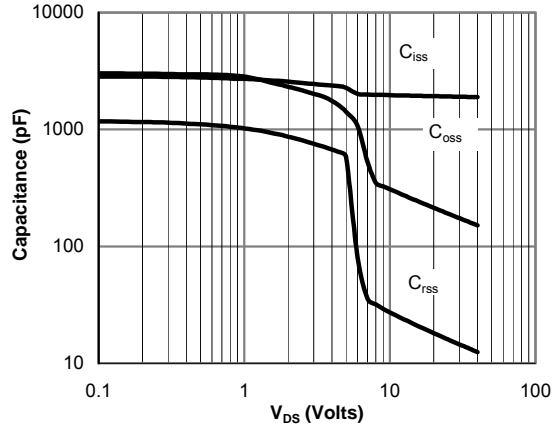


Figure 8: Capacitance Characteristics

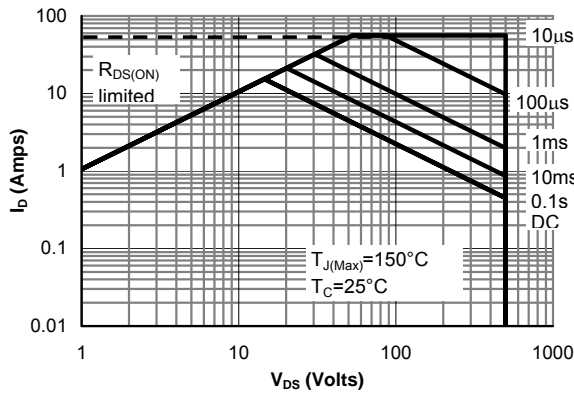


Figure 9: Maximum Forward Biased Safe Operating Area for AOT14N50 (Note F)

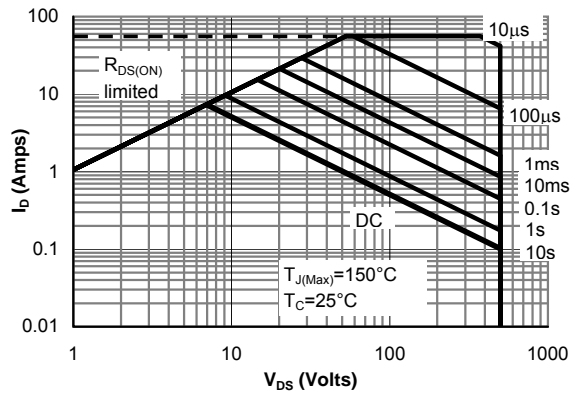


Figure 10: Maximum Forward Biased Safe Operating Area for AOTF14N50 (Note F)

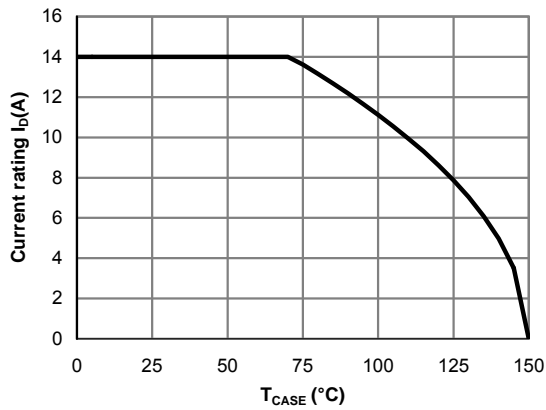


Figure 11: Current De-rating (Note B)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

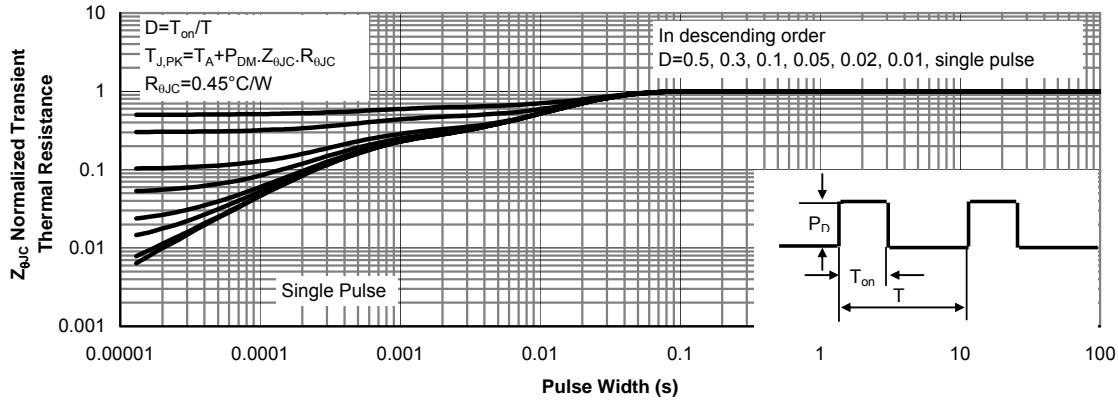


Figure 12: Normalized Maximum Transient Thermal Impedance for AOT14N50 (Note F)

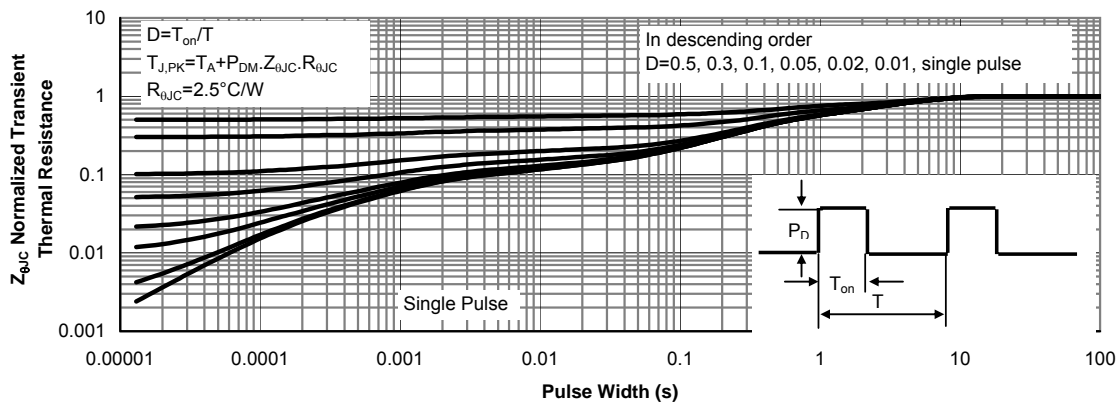
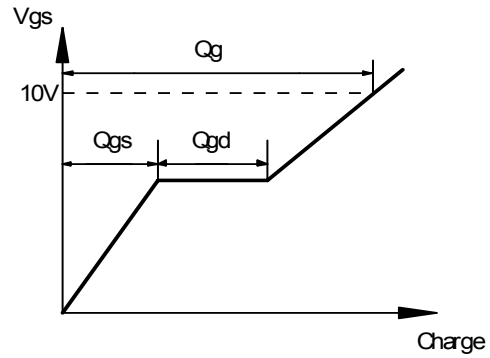
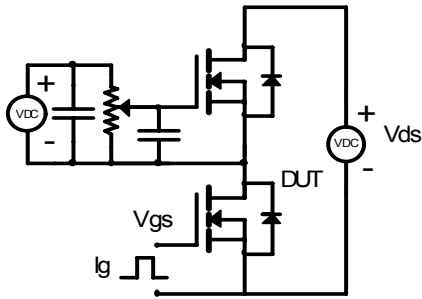
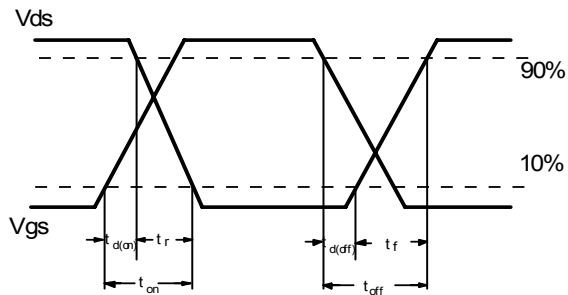
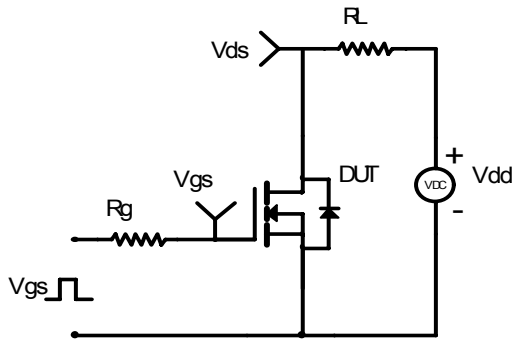


Figure 13: Normalized Maximum Transient Thermal Impedance for AOTF14N50 (Note F)

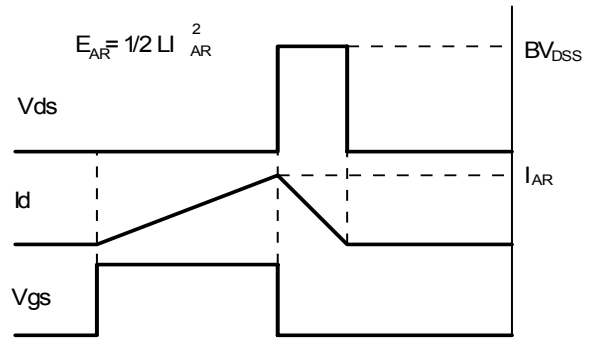
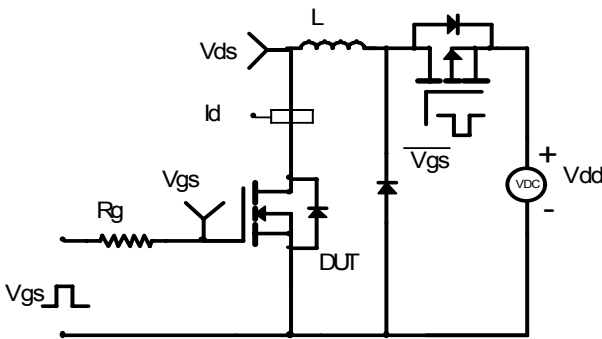
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

